HWET05141P



Ultra-Low Capacitance TVS Protection Dec 2021 Ver. 1.1

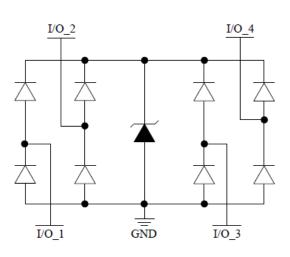
Description

HWET05141P is an ultra-low - capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With Maximum capacitance0.65pF only, HWET05141P is designed to protect parasitic - sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc. HWET05141P uses ultra-small DFN-10L package. Each HWET05141P device can protect four high-speed data lines. The combined features of ultra-low capacitance, ultra-small size and high ESD robustness make HWET05141P ideal for high-speed data ports and high-frequency lines (e.g., HDMI & DVI) applications. The low clamping voltage of the HWET05141P guarantees a minimum stress on the protected IC.

Mechanical Characteristics

- DFN-10L package
- Flammability Rating: UL 94V-0
- Marking: Part number
- Packaging: Tape and Reel

Circuit Diagram



Features

 Transient protection for high-speed data lines IEC 61000-4-2 (ESD) ±25kV (Air) ±17kV (Contact)

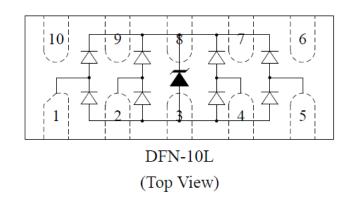
IEC 61000-4-4 (EFT) 40A (5/50 ns) Cable Discharge Event (CDE)

- Package optimized for high-speed lines
- Ultra-small package (2.5mm*1.0mm*0.55mm)
- Protects four data lines
- Low capacitance: 0.4pF Typical(I/O-GND)
- Low leakage current: 0.1µ A @ VRWM (Typ.)
- Low clamping voltage
- Each I/O pin can withstand over 1000 ESD strikes for ±8kV contact discharge

Applications

- Serial ATA
- PCI Express
- Desktops, Servers and Notebooks
- MDDI Ports
- USB2.0/3.0 Power and Data Line Protection
- Display Ports
- High Definition Multi-Media Interface (HDMI)
- Digital Visual Interfaces (DVI)

Pin Configuration



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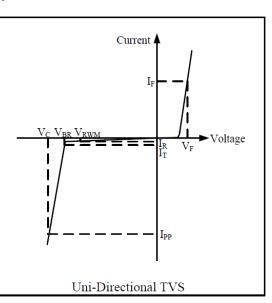
HEXAWAVE

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■Electrical characteristics (Ta = 25 °C)

Symbol	Parameter					
V _{RWM}	Nominal Reverse Working Voltage					
I _R	Reverse Leakage Current @ V_{RWM}					
VBR	V_{BR} Reverse Breakdown Voltage @ I_{T}					
I _T	I _T Test Current for Reverse Breakdown					
V _c	Clamping Voltage @ I _{PP}					
PP	Maximum Peak Pulse Current					
Cesd	Parasitic Capacitance					
V _R	Reverse Voltage					
f	Small Signal Frequency					
l _F	Forward Current					
V _F	Forward Voltage @ I_F					



Symbol	Test Condition	Minimum	Typical	Maximum	Units
Vrwm				5	V
I _R	$V_{RWM} = 5V, T = 25^{\circ}C$ Between I/O and GND		0.1	1	μA
Vbr	$I_{T} = 1mA$ Between I/O and GND	6	8	10	V
V _C	$I_{PP} = 1A$, $t_p = 8/20\mu s$ Between I/O and GND			12	V
Vc	I_{PP} = 8.0A, t_p = 100ns ⁽¹⁾ I_{PP} = 16.0A, t_p = 100ns		14		V
R _{dyn}	IEC61000-4-2 0-6KV, T=25°C Contact, I/O to GND		0.9		Ω
Cesd	VR = 0V, f = 1MHz Between I/O and GND		0.4	0.5	pF
Cesd	$V_R = 0V$, f = 1MHz Between I/O and I/O		0.2	0.25	pF

Absolute Maximum Rating

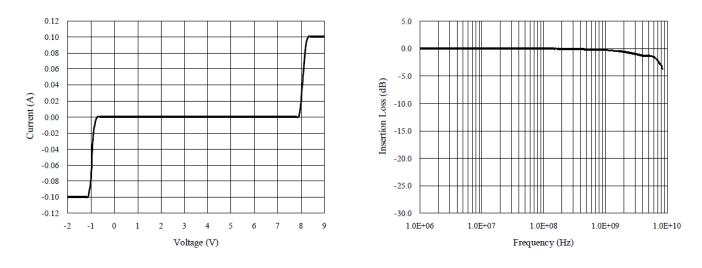
Symbol	Parameter	Value	Units
PP	Peak Pulse Current(tp=8/20us)(I/O pins)	5	А
Vesd	ESD per IEC 61000-4-2 (Air)	±25	kV
	ESD per IEC 61000-4-2 (Contact)	±17	κv
Торт	Operating Temperature	-55/+125	°C
Tstg	Storage Temperature	-55/+150	°C

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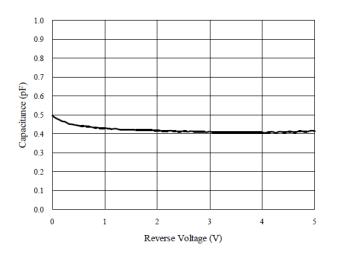
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Insertion Loss S21 of I/O to GND

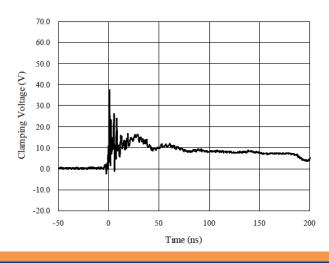


Capacitance vs. Voltage of I/O to GND (f = 1MHz)

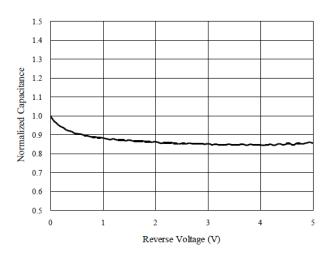
Capacitance vs. Reverse Voltage



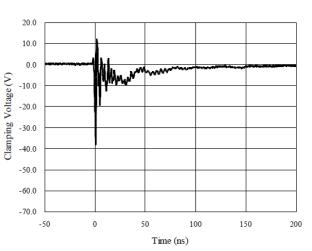
ESD Clamping of I/O to GND (+8kV Contact per IEC 61000-4-2)



Normalized Capacitance vs. Reverse Voltage



ESD Clamping of I/O to GND (-8kV Contact per IEC 61000-4-2)



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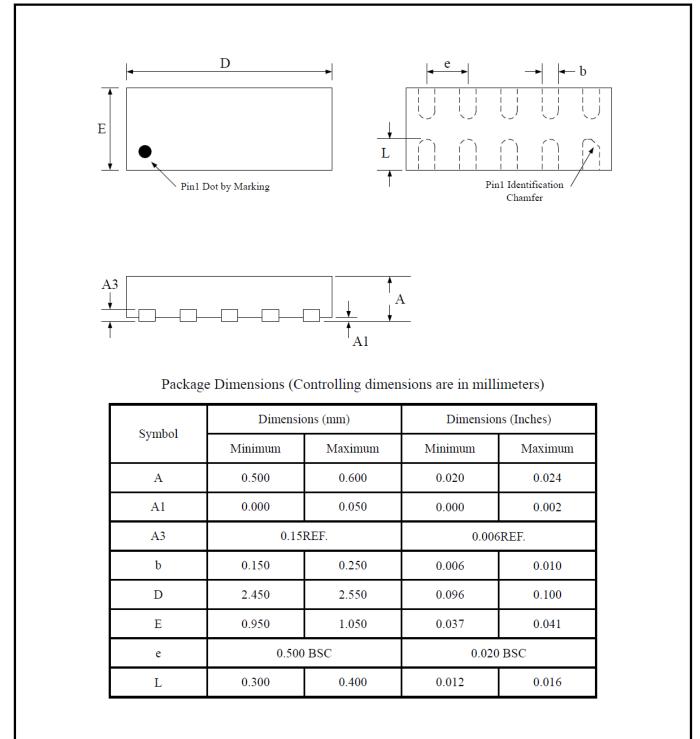
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Package Outline

- DFN-10L package
- **Thermally-Enhanced**
- MSL-1 Level

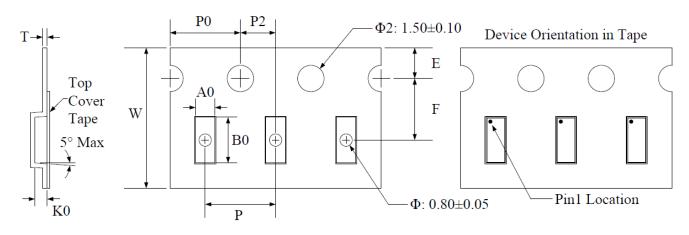




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Tape and Reel Specification



Symbol	W	A0	B0	K0	Е	F	Р	P0	P2	Т
Dimensions (mm)	8.00+0.3 -0.1	1.23±0.05	2.7±0.05	0.7±0.05	1.75±0.1	3.5±0.05	4.0±0.1	4.0±0.1	2.0±0.05	0.25±0.02